

Amendments to the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

Claims 1-12 (Canceled).

Claim 13 (Currently Amended): A semiconductor device comprising:

a substrate;

a transistor having a pair of source/drain regions formed in said substrate and a gate electrode formed via a dielectric film on a channel region sandwiched between said pair of source/drain regions;

an interlayer dielectric film formed on said transistor;

source/drain wirings formed on said interlayer dielectric film; and

conductors formed in said interlayer dielectric film for connecting said source/drain wirings to said source/drain regions, wherein

~~said interlayer dielectric film is formed except for a region between said gate electrode and said conductors, and~~

an opening is formed by selectively removing said interlayer dielectric film between said gate electrode and said conductors, and a material does not exist in said opening.